PSMN059-150Y

N-channel TrenchMOS SiliconMAX standard level FET

3 October 2013 Product data sheet

1. General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

2. Features and benefits

- Higher operating power due to low thermal resistance
- Suitable for high frequency applications due to fast switching characteristics

3. Applications

- Class D amplifier
- DC-to-DC converters
- Motion control
- Switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 150$ °C		-	-	150	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; Fig. 1; Fig. 3		-	-	43	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 2		-	-	113	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 12 A; T_j = 25 °C; Fig. 9; Fig. 10		-	46	59	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 12 A; V_{DS} = 75 V; Fig. 11; Fig. 12		-	9.1	-	nC

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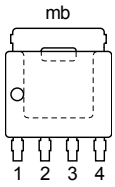
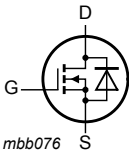
5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 **LFPAK56; Power-SO8 (SOT669)**	
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN059-150Y	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN059-150Y	059150

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 150$ °C		-	150	V
V_{DGR}	drain-gate voltage	$T_j \geq 25$ °C; $T_j \leq 150$ °C; $R_{GS} = 20$ Ω		-	150	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$V_{GS} = 10$ V; $T_{mb} = 25$ °C; Fig. 1; Fig. 3		-	43	A
		$V_{GS} = 10$ V; $T_{mb} = 100$ °C; Fig. 1		-	27.7	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10$ µs; $T_{mb} = 25$ °C; Fig. 3		-	129	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; Fig. 2		-	113	W
T_{stg}	storage temperature			-55	150	°C

Symbol	Parameter	Conditions		Min	Max	Unit
T_j	junction temperature			-55	150	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C		-	52	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; T_{mb} = 25 °C		-	208	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 12.1 A; $V_{sup} \leq 150$ V; unclamped; t_p = 0.21 ms; R_{GS} = 50 Ω		-	255	mJ

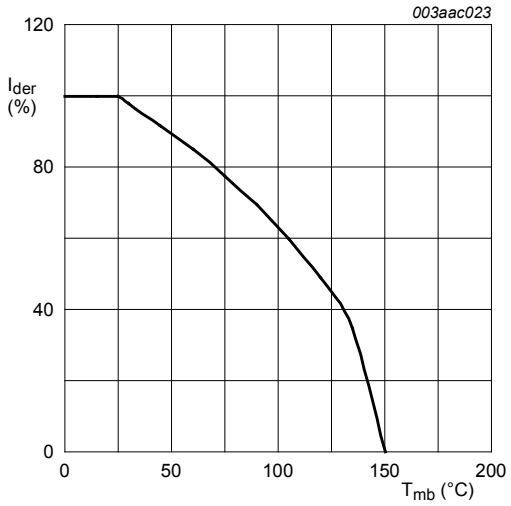


Fig. 1. Normalized continuous drain current as a function of mounting base temperature

$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\,\%$$

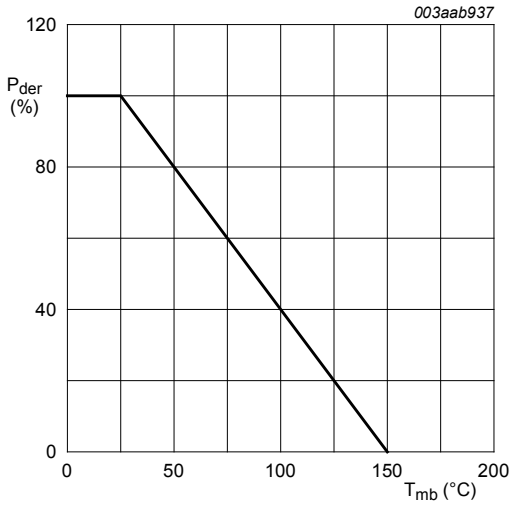


Fig. 2. Normalized total power dissipation as a function of solder point temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

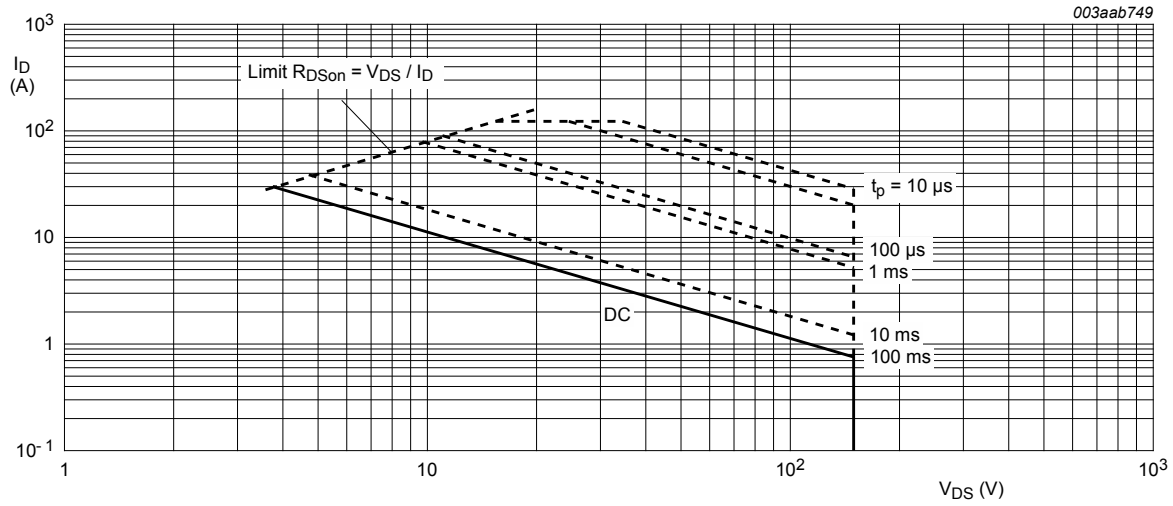


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25\,°C; I_{DM}$ is single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	mounted on a printed-circuit board; vertical in still air; Fig. 4		-	-	1.1	K/W

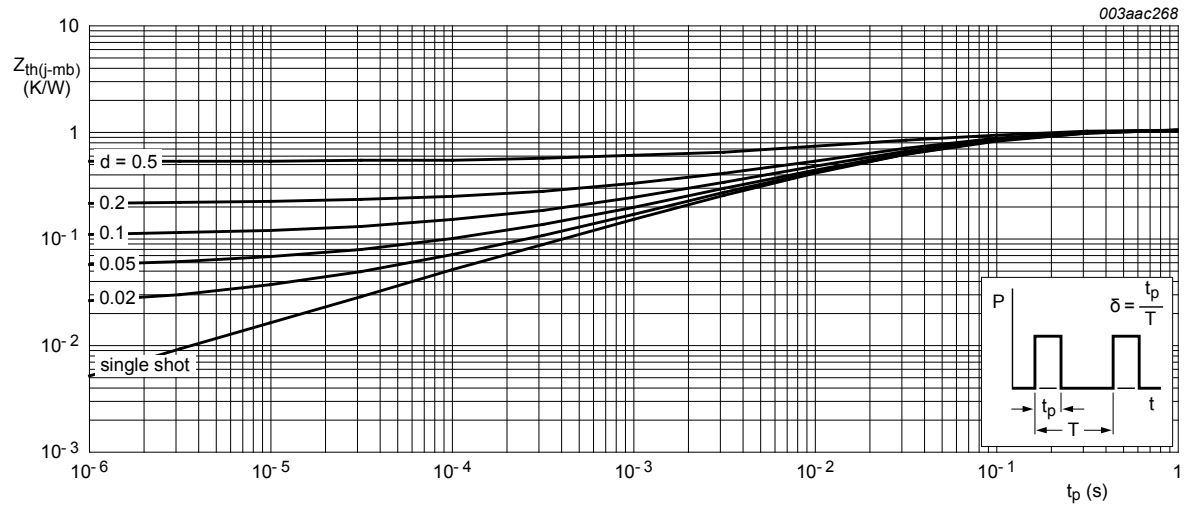


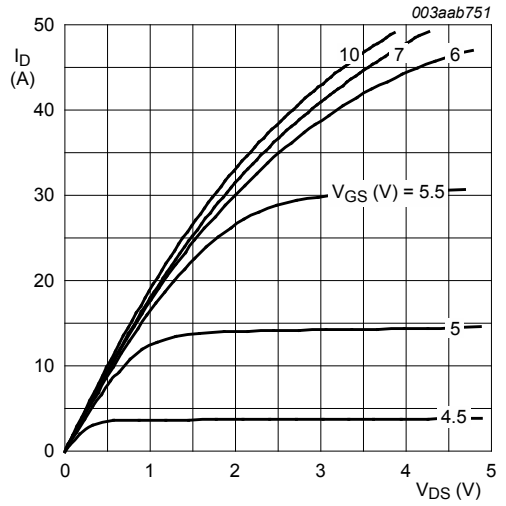
Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

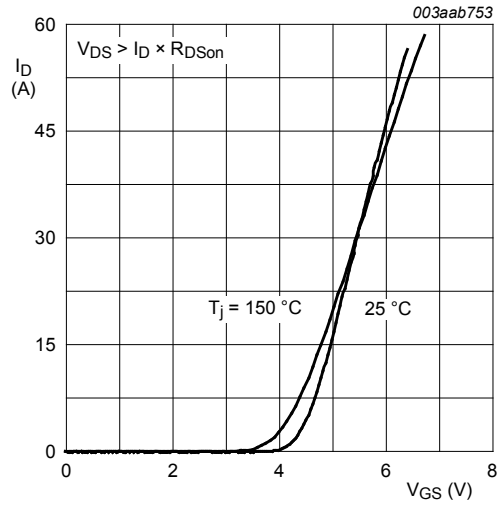
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		150	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		133	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; Fig. 7; Fig. 8		2	3	4	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 150 °C; Fig. 7; Fig. 8		1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; Fig. 7; Fig. 8		-	-	4.4	V
I_{DSS}	drain leakage current	V_{DS} = 120 V; V_{GS} = 0 V; T_j = 25 °C		-	-	1	µA
		V_{DS} = 120 V; V_{GS} = 0 V; T_j = 150 °C		-	-	100	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	-	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	-	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 12 A; T_j = 25 °C; Fig. 9; Fig. 10		-	46	59	mΩ
		V_{GS} = 10 V; I_D = 12 A; T_j = 150 °C; Fig. 9; Fig. 10		-	101	135	mΩ
R_G	gate resistance	f = 1 MHz		-	1.1	-	Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 12 A; V_{DS} = 75 V; V_{GS} = 10 V; Fig. 11; Fig. 12		-	27.9	-	nC
Q_{GS}	gate-source charge			-	6.3	-	nC
Q_{GD}	gate-drain charge			-	9.1	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I_D = 12 A; V_{DS} = 75 V; Fig. 11; Fig. 12		-	4.8	-	V
C_{iss}	input capacitance	V_{DS} = 30 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; Fig. 13		-	1529	-	pF
C_{oss}	output capacitance			-	208	-	pF
C_{rss}	reverse transfer capacitance			-	66	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 75 V; R_L = 3 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 5.6 Ω		-	14.2	-	ns
t_r	rise time			-	42	-	ns
$t_{d(off)}$	turn-off delay time			-	54.2	-	ns
t_f	fall time			-	11.1	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 12 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 14		-	0.9	1.2	V

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
t_{rr}	reverse recovery time	I_S = 12 A; dI_S/dt = -100 A/μs; V_{GS} = 0 V; V_{DS} = 30 V		-	67	-	ns
Q_r	recovered charge	I_S = 12 A; dI_S/dt = -100 A/μs; V_{GS} = 0 V		-	226	-	nC



T_j = 25 °C

Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values



T_j = 25 °C and 150 °C; $V_{DS} > I_D \times R_{DSon}$

Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

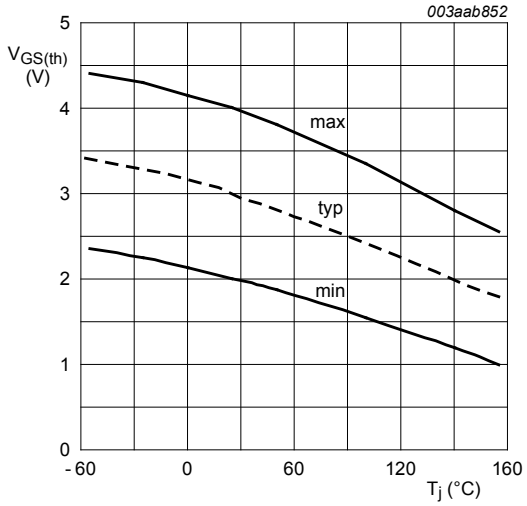


Fig. 7. Gate-source threshold voltage as a function of junction temperature

$I_D = 1mA; V_{DS} = V_{GS}$

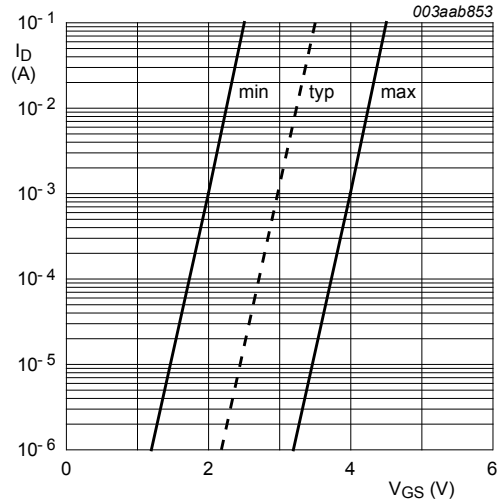


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25\,°C; V_{DS} = 5V$

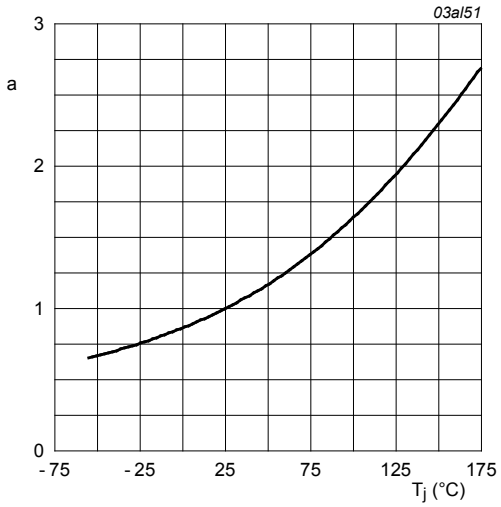


Fig. 9. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

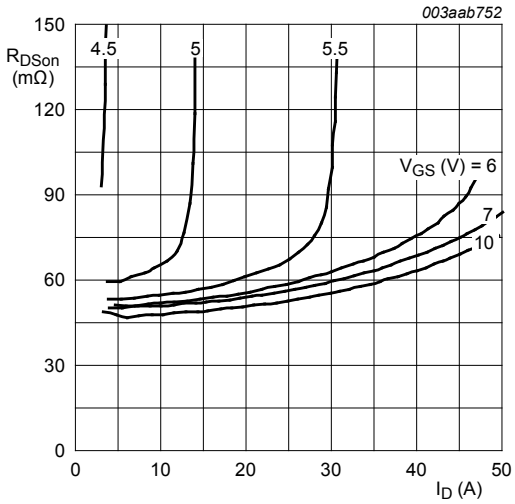


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25\,°C$$

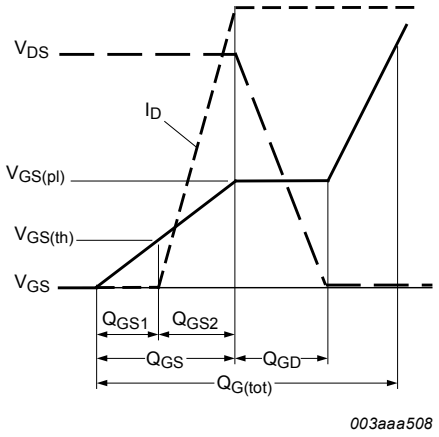


Fig. 11. Gate charge waveform definitions

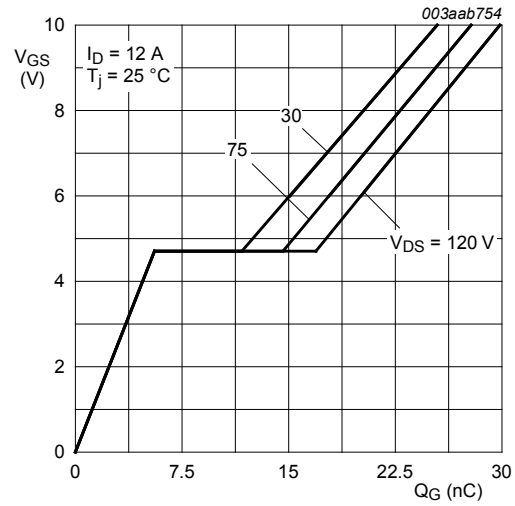


Fig. 12. Gate-source voltage as a function of gate charge; typical values

$$I_D = 12\,A;\ V_{DS} = 30, 75\ and\ 120\,V$$

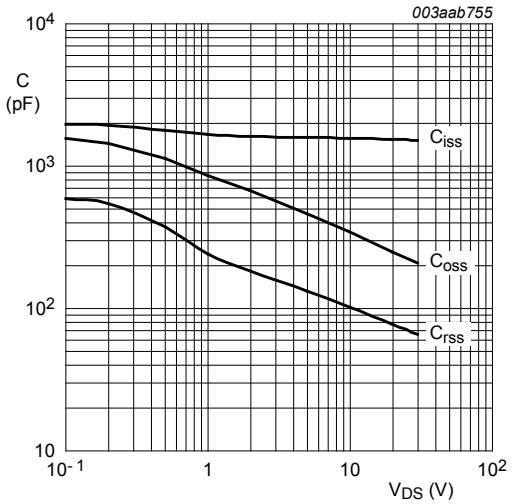


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0V; f = 1MHz$

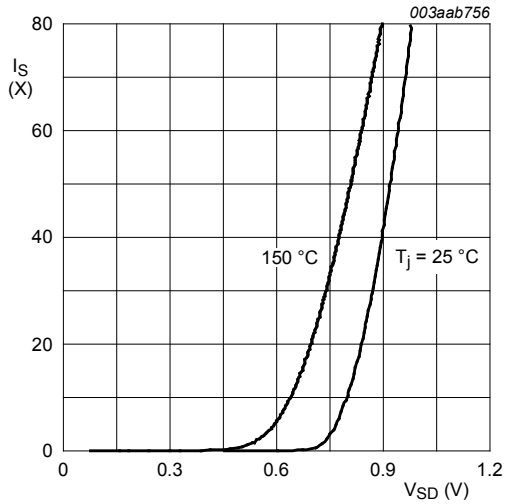
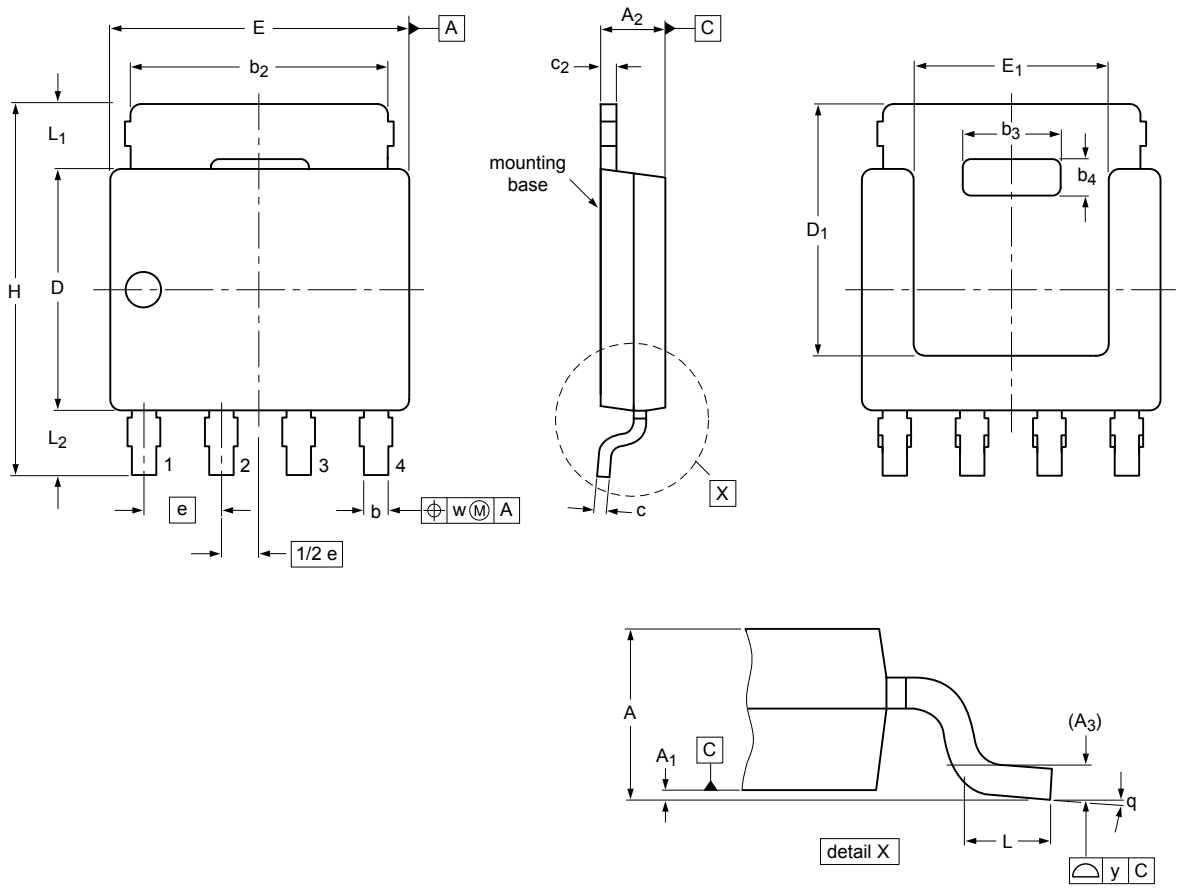


Fig. 14. Source current as a function of source-drain voltage; typical values

$T_j = 25°C$ and $150°C; V_{GS} = 0V$

11. Package outline

Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads **SOT669**



Dimensions (mm are the original dimensions)

Unit[1]		A	A_1	A_2	A_3	b	b_2	b_3	b_4	c	c_2	$D^{(1)}$	$D_1{}^{(1)}$	$E^{(1)}$	$E_1{}^{(1)}$	e	H	L	L_1	L_2	w	y
mm	max	1.20	0.15	1.10		0.50	4.41	2.2	0.9	0.25	0.30	4.10	4.20	5.0	3.3		6.2	0.85	1.3	1.3		
	nom				0.25											1.27					0.25	0.1
	min	1.01	0.00	0.95		0.35	3.62	2.0	0.7	0.19	0.24	3.80		4.8	3.1		5.8	0.40	0.8	0.8		

θ
8°
0°

Note
1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

sot669_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT669		MO-235				~~11-03-25~~ 13-02-27

Fig. 15. Package outline LFPAK56; Power-SO8 (SOT669)

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 3 October 2013